

L A Coldren

List of Publications by Year in descending order

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163
papers

7,168
citations

57631

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164
all docs

164
docs citations

164
times ranked

3706
citing authors

#	ARTICLE	IF	CITATIONS
1	Picosecond Coherent Optical Manipulation of a Single Electron Spin in a Quantum Dot. <i>Science</i> , 2008, 320, 349-352.	6.0	473
2	Effective band gap inhomogeneity and piezoelectric field in InGaN/GaN multiquantum well structures. <i>Applied Physics Letters</i> , 1998, 73, 2006-2008.	1.5	427
3	Optical Anisotropy in a Quantum-Well-Wire Array with Two-Dimensional Quantum Confinement. <i>Physical Review Letters</i> , 1989, 62, 466-469.	2.9	371
4	Two-dimensional free-space beam steering with an optical phased array on silicon-on-insulator. <i>Optics Express</i> , 2011, 19, 21595.	1.7	350
5	Fully integrated hybrid silicon two dimensional beam scanner. <i>Optics Express</i> , 2015, 23, 5861.	1.7	262
6	Indium tin oxide contacts to gallium nitride optoelectronic devices. <i>Applied Physics Letters</i> , 1999, 74, 3930-3932.	1.5	226
7	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. <i>Applied Physics Letters</i> , 1988, 53, 1378-1380.	1.5	222
8	Surface migration induced self-aligned InAs islands grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995, 66, 1620-1622.	1.5	180
9	Nondestructive Optical Measurements of a Single Electron Spin in a Quantum Dot. <i>Science</i> , 2006, 314, 1916-1920.	6.0	180
10	Growth and characterization of bulk InGaN films and quantum wells. <i>Applied Physics Letters</i> , 1996, 68, 3147-3149.	1.5	156
11	Monolithic two-section GaInAsP/InP active optical resonator devices formed by reactive ion etching. <i>Applied Physics Letters</i> , 1981, 38, 315-317.	1.5	140
12	Measured and calculated radiative lifetime and optical absorption of $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ quantum structures. <i>Physical Review B</i> , 2000, 61, 10994-11008.	1.1	137
13	Theoretical gain in strained InGaAs/AlGaAs quantum wells including valence band mixing effects. <i>Applied Physics Letters</i> , 1990, 57, 2835-2837.	1.5	135
14	Optically detected coherent spin dynamics of a single electron in a quantum dot. <i>Nature Physics</i> , 2007, 3, 770-773.	6.5	121
15	GaInAsP/InP stripe geometry laser with a reactive ion etched facet. <i>Applied Physics Letters</i> , 1980, 37, 681-683.	1.5	108
16	Spontaneous growth of coherent tilted superlattice on vicinal (100) GaAs substrates. <i>Applied Physics Letters</i> , 1989, 54, 1690-1692.	1.5	105
17	Bandgap engineered digital alloy interfaces for lower resistance vertical cavity surface emitting lasers. <i>Applied Physics Letters</i> , 1993, 63, 3411-3413.	1.5	93
18	Large and small signal dynamics of vertical cavity surface emitting lasers. <i>Applied Physics Letters</i> , 1993, 62, 325-327.	1.5	87

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19	Demonstration of broadband tunability in a semiconductor laser using sampled gratings. Applied Physics Letters, 1992, 60, 2321-2323.	1.5	81
20	Self-electro-optic device based on a superlattice asymmetric Fabry-Perot modulator with an on/off ratio $\approx 100:1$. Applied Physics Letters, 1990, 57, 1345-1347.	1.5	76
21	Minimum temperature sensitivity of 1.55 μm vertical-cavity lasers at $\sim 30\%$ gain offset. Applied Physics Letters, 1998, 72, 1814-1816.	1.5	76
22	Estimation of scattering losses in dielectrically apertured vertical cavity lasers. Applied Physics Letters, 1996, 68, 1757-1759.	1.5	73
23	Single-mode operation of coupled-cavity GaInAsP/InP semiconductor lasers. Applied Physics Letters, 1983, 42, 6-8.	1.5	69
24	Directional reactive ion etching at oblique angles. Applied Physics Letters, 1980, 36, 583-585.	1.5	67
25	Externally Mode-Matched Cavity Quantum Electrodynamics with Charge-Tunable Quantum Dots. Physical Review Letters, 2009, 102, 097403.	2.9	67
26	Lateral carrier diffusion and surface recombination in InGaAs/AlGaAs quantum-well ridge-waveguide lasers. Journal of Applied Physics, 1994, 76, 4479-4487.	1.1	66
27	Effects of Si-doping in the barriers of InGaN multiquantum well purplish-blue laser diodes. Applied Physics Letters, 1998, 73, 496-498.	1.5	66
28	Two-Dimensional Optical Beam Steering With InP-Based Photonic Integrated Circuits. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 6100212-6100212.	1.9	66
29	Electrorefraction in GaAs and InGaAsP and its application to phase modulators. Journal of Applied Physics, 1987, 61, 2430-2433.	1.1	65
30	Chemical Mechanical Polishing of Gallium Nitride. Electrochemical and Solid-State Letters, 2002, 5, G61.	2.2	63
31	Parallel free-space optical interconnect based on arrays of vertical-cavity lasers and detectors with monolithic microlenses. Applied Optics, 1998, 37, 2811.	2.1	62
32	Analysis of multielement semiconductor lasers. Journal of Applied Physics, 1983, 54, 2962-2969.	1.1	60
33	Gain spectroscopy on InGaN/GaN quantum well diodes. Applied Physics Letters, 1997, 70, 2580-2582.	1.5	60
34	Improved characteristics of InGaN multiple-quantum-well laser diodes grown on laterally epitaxially overgrown GaN on sapphire. Applied Physics Letters, 2000, 76, 529-531.	1.5	59
35	Reactive ion beam etching of InP with Cl_2 . Applied Physics Letters, 1981, 38, 264-266.	1.5	58
36	Normally-off high-contrast asymmetric Fabry-Perot reflection modulator using Wannier-Stark localization in a superlattice. Applied Physics Letters, 1990, 56, 1886-1888.	1.5	57

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37	Directional reactive-ion etching of InP with Cl ₂ containing gases. Journal of Vacuum Science and Technology, 1981, 19, 225-230.	1.9	54
38	Epitaxially-stacked multiple-active-region 1.55-μm lasers for increased differential efficiency. Applied Physics Letters, 1999, 74, 3251-3253.	1.5	54
39	Hybrid III/V silicon photonic source with integrated 1D free-space beam steering. Optics Letters, 2012, 37, 4257.	1.7	53
40	Surface energy model for the thickness dependence of the lateral oxidation of AlAs. Journal of Applied Physics, 1997, 82, 2277-2280.	1.1	51
41	High modulation efficiency of intracavity contacted vertical cavity lasers. Applied Physics Letters, 1994, 65, 1483-1485.	1.5	50
42	Technique for integration of vertical cavity lasers and resonant photodetectors. Applied Physics Letters, 1998, 73, 1-3.	1.5	50
43	Electrically tunable Fabry-Perot mirror using multiple quantum well index modulation. Applied Physics Letters, 1988, 53, 637-639.	1.5	49
44	88-Å, continuous-wave operation of apertured, intracavity contacted, 1.55 μm vertical-cavity surface-emitting lasers. Applied Physics Letters, 2001, 78, 1337-1339.	1.5	49
45	MONOLITHIC ACOUSTIC SURFACE-WAVE AMPLIFIER. Applied Physics Letters, 1971, 18, 317-319.	1.5	48
46	Highly efficient waveguide phase modulator for integrated optoelectronics. Applied Physics Letters, 1986, 48, 1243-1245.	1.5	46
47	Theoretical gain in compressive and tensile strained InGaAs/InGaAsP quantum wells. Applied Physics Letters, 1991, 59, 588-590.	1.5	45
48	Evaluating the effects of optical and carrier losses in etched-post vertical cavity lasers. Journal of Applied Physics, 1995, 78, 5871-5875.	1.1	44
49	An Integrated 40 Gbit/s Optical Costas Receiver. Journal of Lightwave Technology, 2013, 31, 2244-2253.	2.7	44
50	High-efficiency TEM ₀₀ continuous-wave (Al,Ga)As epitaxial surface-emitting lasers and effect of half-wave periodic gain. Applied Physics Letters, 1989, 54, 1209-1211.	1.5	42
51	Near-room-temperature continuous-wave operation of multiple-active-region 1.55 μm vertical-cavity lasers with high differential efficiency. Applied Physics Letters, 2000, 77, 3137-3139.	1.5	41
52	Transverse modulators with a record reflection change of >20%/V using asymmetric Fabry-Perot structures. Applied Physics Letters, 1990, 56, 1626-1628.	1.5	39
53	Dielectric apertures as intracavity lenses in vertical-cavity lasers. Applied Physics Letters, 1996, 68, 313-315.	1.5	39
54	Design parameters for lateral carrier confinement in quantum-dot lasers. Applied Physics Letters, 1999, 74, 2752-2754.	1.5	38

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55	Terahertz electro-optic wavelength conversion in GaAs quantum wells: Improved efficiency and room-temperature operation. Applied Physics Letters, 2004, 84, 840-842.	1.5	37
56	On the Formation of Planar Etched Facets in GaInAsP/InP Double Heterostructures. Journal of the Electrochemical Society, 1983, 130, 1918-1926.	1.3	36
57	Disordering of GaAs/AlGaAs multiple quantum well structures by thermal annealing for monolithic integration of laser and phase modulator. Applied Physics Letters, 1989, 55, 672-674.	1.5	36
58	Generation of picosecond pulses with a gain-switched GaAs surface-emitting laser. Applied Physics Letters, 1990, 57, 963-965.	1.5	33
59	Voltage-controlled wavelength conversion by terahertz electro-optic modulation in double quantum wells. Applied Physics Letters, 2002, 81, 1564-1566.	1.5	33
60	Room-temperature two-dimension exciton exchange and blue shift of absorption edge in GaAs/AlGaAs superlattices under an electric field. Applied Physics Letters, 1989, 54, 1549-1551.	1.5	31
61	Effect of bias field in a zinc-oxide-on-silicon acoustic convolver. Applied Physics Letters, 1974, 25, 473-475.	1.5	29
62	Efficient vertical-cavity lasers. Optical and Quantum Electronics, 1992, 24, S105-S119.	1.5	29
63	Modeling the current to light characteristics of index-guided vertical-cavity surface-emitting lasers. Applied Physics Letters, 1993, 62, 1050-1052.	1.5	28
64	High-efficiency and low-threshold InGaAs/AlGaAs quantum-well lasers. Journal of Applied Physics, 1994, 76, 3932-3934.	1.1	27
65	Contribution of the band-filling effect to the effective refractive index change in double-heterostructure GaAs/AlGaAs phase modulators. Journal of Applied Physics, 1987, 62, 4548-4553.	1.1	25
66	Wide-bandwidth, high-efficiency reflection modulators using an unbalanced Fabry-Perot structure. Applied Physics Letters, 1989, 55, 1946-1948.	1.5	25
67	Many body effects in the temperature dependence of threshold in a vertical-cavity surface-emitting laser. Applied Physics Letters, 1995, 66, 2460-2462.	1.5	25
68	Design of optimized high-speed depletion-edge translation optical waveguide modulators in III-V semiconductors. Applied Physics Letters, 1987, 51, 792-794.	1.5	24
69	Calibrated intensity noise measurements in microcavity laser diodes. Applied Physics Letters, 1995, 67, 3697-3699.	1.5	24
70	cw monolithic acoustic surface wave amplifier incorporated in a $\lambda/4$ waveguide. Applied Physics Letters, 1973, 23, 117-118.	1.5	23
71	Acoustic waveguide with a cladded core geometry. Applied Physics Letters, 1975, 26, 31-34.	1.5	23
72	Optimum coupling junction and cavity lengths for coupled-cavity semiconductor lasers. Journal of Applied Physics, 1985, 57, 740-754.	1.1	23

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73	Effect of layer thickness variations on the performance of asymmetric Fabry-Perot reflection modulators. Journal of Applied Physics, 1992, 72, 855-860.	1.1	23
74	Tertiarybutylarsine and tertiarybutylphosphine for the MOCVD growth of low threshold 1.55 μ m In _x Ga _{1-x} As/InP quantum-well lasers. Journal of Electronic Materials, 1994, 23, 87-91.	1.0	23
75	Stabilization and optimum biasing of dynamic single-mode coupled cavity lasers. Applied Physics Letters, 1984, 44, 169-171.	1.5	22
76	Zinc oxide on silicon acoustically scanned imager with positive sensitivity and storage capabilities. Applied Physics Letters, 1975, 27, 6-8.	1.5	21
77	Cleaved coupled cavity lasers with large cavity length ratios for enhanced stability. Applied Physics Letters, 1984, 44, 821-823.	1.5	21
78	Effect of temperature on the operating characteristics of asymmetric Fabry-Perot reflection modulators. Applied Physics Letters, 1990, 57, 267-269.	1.5	21
79	Temperature dependent threshold and modulation characteristics in InGaAs/GaAs quantum well ridge waveguide lasers. Applied Physics Letters, 1995, 66, 2040-2042.	1.5	21
80	GaAs/AlGaAs multiple quantum well field induced optical waveguide. Applied Physics Letters, 1990, 57, 114-116.	1.5	20
81	Reduced lateral carrier diffusion for improved miniature semiconductor lasers. Journal of Applied Physics, 1997, 81, 3377-3381.	1.1	20
82	Resonant-cavity InGaAs/InAlGaAs/InP photodetector arrays for wavelength demultiplexing applications. Applied Physics Letters, 1997, 70, 2347-2349.	1.5	20
83	Electronically variable delay using ferroelastic ferroelectrics. Applied Physics Letters, 1977, 30, 506-508.	1.5	19
84	Continuous operation of monolithic dynamic single-mode coupled cavity lasers. Applied Physics Letters, 1984, 44, 368-370.	1.5	19
85	Tight binding analysis on exciton binding energy in field induced Stark localized superlattices. Applied Physics Letters, 1989, 55, 2002-2004.	1.5	19
86	Analysis and optimization of graded index separate confinement heterostructure waveguides for quantum well lasers. Journal of Applied Physics, 1991, 69, 2857-2861.	1.1	19
87	Optical gain anisotropy in serpentine superlattice nanowire array lasers. Applied Physics Letters, 1993, 63, 2015-2017.	1.5	19
88	Radical beam/ion beam etching of GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1885.	1.6	18
89	Low threshold high efficiency high yield impurity induced layer disordering laser by self aligned Si/Zn diffusion. Applied Physics Letters, 1990, 57, 2534-2536.	1.5	18
90	Photonic integrated tunable receivers with optical preamplifiers for direct detection. Applied Physics Letters, 1993, 63, 880-882.	1.5	18

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91	Strong-field terahertz optical mixing in excitons. <i>Physical Review B</i> , 2003, 67, .	1.1	18
92	Optically addressed spatial light modulators by MBE-grown nipi MQW structures. <i>Applied Optics</i> , 1989, 28, 4801.	2.1	16
93	Terahertz optical mixing in biased GaAs single quantum wells. <i>Physical Review B</i> , 2004, 70, .	1.1	16
94	Zinc oxide on silicon memory cells scanned by acoustic surface waves. <i>Applied Physics Letters</i> , 1975, 26, 137-139.	1.5	15
95	Observation of anomalously large blue shift of the heavy-hole photocurrent peak and optical bistability in narrow asymmetric coupled quantum wells. <i>Applied Physics Letters</i> , 1991, 59, 1025-1027.	1.5	15
96	Low regrowth interface recombination rates in InGaAs/GaAs buried ridge lasers fabricated by in situ processing. <i>Applied Physics Letters</i> , 1995, 66, 1966-1968.	1.5	15
97	Interior surface acoustic waveguiding in capillaries. <i>Applied Physics Letters</i> , 1974, 25, 324-326.	1.5	14
98	Molecular-beam epitaxy growth of high-quality active regions with strained In _x Ga _{1-x} As quantum wells and lattice-matched Al _x Ga _{1-x} In _{(1-x)y} As barriers using submonolayer superlattices. <i>Applied Physics Letters</i> , 2002, 80, 3509-3511.	1.5	14
99	Power-Efficient Kerr Frequency Comb Based Tunable Optical Source. <i>IEEE Photonics Journal</i> , 2017, 9, 1-14.	1.0	14
100	Reconfigurable optical properties in InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , 1997, 71, 1455-1457.	1.5	13
101	Reduced dynamic linewidth in three-terminal two-section diode lasers. <i>Applied Physics Letters</i> , 1985, 46, 125-127.	1.5	12
102	Continuous tunability in three-terminal coupled-cavity lasers. <i>Applied Physics Letters</i> , 1986, 48, 1190-1192.	1.5	12
103	Optically controlled reflection modulator using GaAs/AlGaAs n-i-p-i/multiple-quantum-well structures. <i>Optics Letters</i> , 1989, 14, 230.	1.7	12
104	Design, fabrication and characterization of high-speed asymmetric Fabry-Perot modulators for optical interconnect applications. <i>Optical and Quantum Electronics</i> , 1993, 25, S885-S898.	1.5	12
105	Coupled-cavity resonant photodetectors for high-performance wavelength demultiplexing applications. <i>Applied Physics Letters</i> , 1997, 71, 178-180.	1.5	12
106	Terahertz-optical mixing in undoped and doped GaAs quantum wells: From excitonic to electronic intersubband transitions. <i>Physical Review B</i> , 2005, 72, .	1.1	12
107	Fully integrated hybrid silicon free-space beam steering source with 32-channel phased array. <i>Proceedings of SPIE</i> , 2014, , .	0.8	12
108	Variable frequency SAW resonators on ferroelectric/ferroelastics. <i>Applied Physics Letters</i> , 1978, 32, 129-131.	1.5	11

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109	Etched groove coupled cavity vapor phase transported window lasers at 1.55 μ m. Applied Physics Letters, 1985, 46, 5-7.	1.5	10
110	Behavior of SiNx films as masks for Zn diffusion. Journal of Applied Physics, 1987, 62, 828-831.	1.1	10
111	Effect of AlGaIn/GaN Strained Layer Superlattice Period on InGaIn MQW Laser Diodes. Physica Status Solidi A, 1999, 176, 59-62.	1.7	10
112	Analog read only memory using gadolinium molybdate. Applied Physics Letters, 1978, 33, 373-375.	1.5	9
113	Silicon diffusion into Al _x Ga _{1-x} As (x=0-0.4) from a sputtered silicon film. Applied Physics Letters, 1987, 50, 265-266.	1.5	9
114	Measurement of gain current relations for InGaIn multiple quantum wells. Applied Physics Letters, 1998, 73, 3887-3889.	1.5	9
115	Catastrophic optical damage in GaInN multiple quantum wells. Applied Physics Letters, 1998, 72, 3267-3269.	1.5	9
116	High-differential-quantum-efficiency, long-wavelength vertical-cavity lasers using five-stage bipolar-cascade active regions. Applied Physics Letters, 2005, 86, 211104.	1.5	9
117	TRAPPING MODEL FOR InSb THIN FILMS. Applied Physics Letters, 1971, 18, 319-321.	1.5	8
118	Optoelectronic properties of coupled cavity semiconductor lasers. Applied Physics Letters, 1984, 44, 735-737.	1.5	8
119	Use of independently controlled Cl radical and Ar ion beams for anisotropic chemically enhanced etching of GaAs. Applied Physics Letters, 1988, 53, 2308-2310.	1.5	8
120	Impurity induced disordered phase modulators in AlGaAs/GaAs quantum well and double heterostructure waveguides. Applied Physics Letters, 1988, 53, 728-730.	1.5	8
121	High contrast, large optical bandwidth field induced guide/antiguide modulator. Applied Physics Letters, 1991, 58, 2211-2213.	1.5	8
122	Analysis and optimization of quantum well thickness for GaAs/AlGaAs and InGaAs/GaAs/AlGaAs quantum well lasers. Journal of Applied Physics, 1992, 72, 5047-5054.	1.1	8
123	Increased lateral oxidation rates of AlInAs on InP using short-period superlattices. Journal of Electronic Materials, 2000, 29, 1100-1104.	1.0	8
124	Molecular beam epitaxial growth of monolithic 1.55 μ m vertical cavity surface emitting lasers with AlGaAsSb/AlAsSb Bragg mirrors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1601.	1.6	8
125	Enhanced wavelength tuning of an InGaAsP-InP laser with a thermal-strain-magnifying trench. Applied Physics Letters, 2000, 77, 2629-2631.	1.5	8
126	Self aligned Si-Zn diffusion into GaAs and AlGaAs. Journal of Applied Physics, 1988, 64, 1855-1858.	1.1	7

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127	Asymmetric Fabry-Perot reflection modulators using red- and blue-shifted electroabsorption effects. Journal of Applied Physics, 1990, 68, 875-877.	1.1	7
128	Relating the chirp parameter to the number of quantum wells in GaAs/AlGaAs waveguide modulators. Applied Physics Letters, 1989, 55, 718-720.	1.5	6
129	Al _{0.95} Ga _{0.05} As _{0.56} Sb _{0.44} for lateral oxide-confinement layer in InP-based devices. Applied Physics Letters, 2003, 82, 1329-1331.	1.5	6
130	Selectively etched tunnel junction for lateral current and optical confinement in InP-based vertical cavity lasers. Journal of Electronic Materials, 2004, 33, 118-122.	1.0	6
131	Intensity noise and facet correlation in Fabry-Perot laser diodes with low facet reflectivities. Applied Physics Letters, 1995, 66, 3419-3421.	1.5	5
132	Vertical-cavity surface-emitting lasers for free-space interconnects. , 1996, 10284, 8.		5
133	Individually optimized bottom-emitting vertical-cavity lasers and bottom-illuminated resonant photodetectors sharing the same epitaxial structure. Journal of Optics, 1999, 1, 317-319.	1.5	5
134	Rate equations of vertical-cavity semiconductor optical amplifiers. Applied Physics Letters, 2002, 80, 3057-3059.	1.5	5
135	Simultaneous gain and phase-shift enhancements in periodic gain structures. Journal of Applied Physics, 1990, 67, 4387-4389.	1.1	4
136	Molecular beam epitaxial growth of strained AlGaInAs multi-quantum well lasers on InP. Journal of Electronic Materials, 1996, 25, 948-954.	1.0	4
137	Measurement of the AlGaInAs/AlGaAs conduction-band offset using ballistic electron emission spectroscopy. Applied Physics Letters, 1998, 73, 3271-3272.	1.5	4
138	A monolithic diode laser chemical sensor with a quasi-symmetrical sensing waveguide for improved sensitivity. Applied Physics Letters, 2004, 85, 320-322.	1.5	4
139	Sputtered silicon as a new etching mask for GaAs devices. Journal of Applied Physics, 1986, 60, 1218-1220.	1.1	3
140	Dry Etching and Impurity Diffusion for Integrated Optoelectronics. Materials Research Society Symposia Proceedings, 1988, 126, 237.	0.1	3
141	Comparison of quantum-confined Stark effect in interdiffused and abrupt GaAs/AlGaAs quantum wells. Applied Physics Letters, 1989, 55, 2526-2528.	1.5	3
142	Compound-Cavity Lasers For Medium Range Lidar Applications. , 1989, , .		3
143	Effects of Hydrogen on Chlorine Radical-Beam Ion-Beam Etching of Al _x Ga _{1-x} As with Varying Mole Fraction. Journal of the Electrochemical Society, 1993, 140, 1802-1804.	1.3	3
144	Effects of surface recombination on carrier distributions and device characteristics. Journal of Applied Physics, 1995, 78, 3208-3215.	1.1	3

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145	InP-based multiple quantum well structures grown with tertiarybutylarsine (TBA) and tertiarybutylphosphine (TBP): Effects of growth interruptions on structural and optical properties. Journal of Electronic Materials, 1996, 25, 965-971.	1.0	3
146	Photoluminescence characteristics of GaN/InGaN/GaN quantum wells. Journal of Electronic Materials, 1997, 26, 325-329.	1.0	2
147	Fabrication and molecular beam epitaxy regrowth of first-order, high contrast AlGaAs ⁺ GaAs gratings. Journal of Vacuum Science & Technology B, 2006, 24, 1559.	1.3	2
148	Hybrid silicon free-space source with integrated beam steering. Proceedings of SPIE, 2013, , .	0.8	2
149	Single-chip dual-pumped SOA-based phase-sensitive amplifier at 1550nm. , 2015, , .		2
150	High Performance Quantum Well Asymmetric Fabry-Perot Reflection Modulators: Effect of Layer Thickness Variations. Materials Research Society Symposia Proceedings, 1991, 240, 609.	0.1	1
151	High-performance InP/GaAs based photonic integrated circuits. , 2013, , .		1
152	30 Gbps bottom-emitting 1060 nm VCSEL. , 2014, , .		1
153	Verification of coupling gap dependence in coupled-cavity lasers. , 1984, , .		1
154	Wavelength dependence of high-performance AlGaAs/GaAs depletion-edge-translation waveguide phase modulators. , 1987, , .		1
155	Free-Space Optical Interconnect Using Flip-Chip Bonded, Microlensed Arrays of Monolithic Vertical Cavity Lasers and Resonant Photodetectors. , 1999, , .		1
156	Real-time technique for the characterization of tunable single-frequency lasers. Applied Physics Letters, 1988, 52, 2217-2219.	1.5	0
157	Characterization of geometric effects for the guide/antiguide intensity modulator. Journal of Applied Physics, 1992, 72, 4455-4457.	1.1	0
158	Guide/antiguide optical intensity modulator. Optical and Quantum Electronics, 1993, 25, S899-S915.	1.5	0
159	Introduction to the Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1043-1045.	1.9	0
160	Recent Developments in Long-Wavelength VCSELs. , 2001, , .		0
161	Large-extinction-ratio, wide-optical-bandwidth field-induced guide/antiguide modulator. , 1991, , .		0
162	Widely-Tunable and Vertical-Cavity Lasers: DBRs on Different Planes. , 1994, , .		0

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163	Vertical Cavity Lasers with Large Bandwidths at Low Currents for Dense Free-Space Optical Interconnects. , 1999, , .		0